

InGaAs APD

G14858-0020AA



InGaAs APD that greatly reduces dark current

This InGaAs APD (avalanche photodiode) greatly reduces dark current over existing products by the use of a new device structure and improved processing. The G14858-0020AA is used for distance measurement, low-light-level detection, and so on.

Features

- Low dark current
- Low capacitance
- High sensitivity

Applications

- Distance measurement
- Low-light-level detection

Structure

| Parameter | Specification | Unit |
|---------------------|---|------|
| Window material | Borosilicate glass (AR coated: 1.55 μm) | - |
| Package | TO-18 | - |
| Photosensitive area | φ0.2 | mm |

Absolute maximum ratings

| Parameter | Symbol | Specification | Unit |
|-------------------------|-----------|---------------|------|
| Reverse current | I_R max | 2 | mA |
| Forward current | I_F max | 10 | mA |
| Operating temperature*1 | T_{opr} | -40 to +85 | °C |
| Storage temperature*1 | T_{stg} | -55 to +125 | °C |

*1: No dew condensation

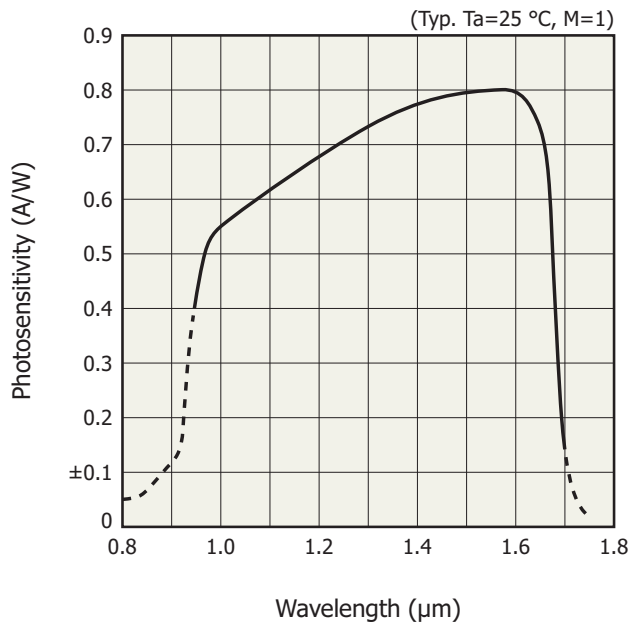
Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

Electrical and optical characteristics (Ta=25 °C)

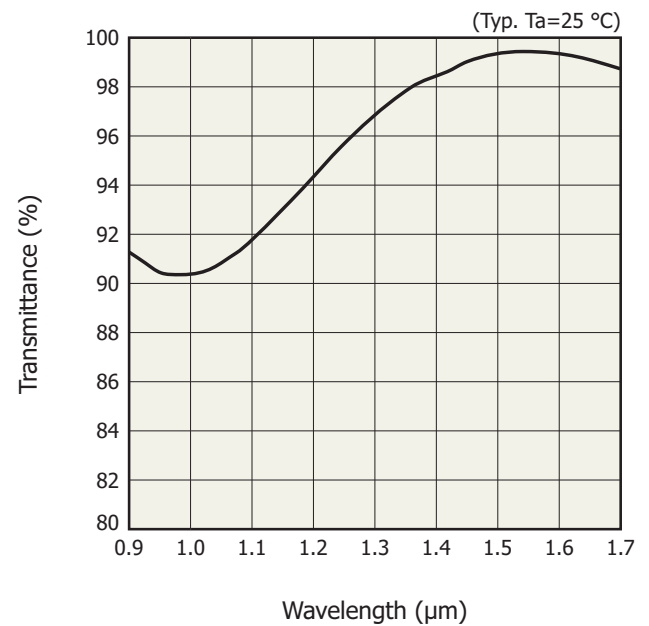
| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit |
|--|-----------------|---|------|-------------|------|----------|
| Spectral response range | λ | | - | 0.95 to 1.7 | - | μm |
| Peak sensitivity wavelength | λ_p | | - | 1.55 | - | μm |
| Photosensitivity | S | $\lambda=1.55 \mu\text{m}, M=1$ | 0.65 | 0.8 | - | A/W |
| Dark current | I_D | $V_R=V_{BR} \times 0.95$ | - | 20 | 50 | nA |
| Temperature coefficient of dark current | ΔT_{ID} | $V_R=V_{BR} \times 0.95$ | - | 1.07 | - | times/°C |
| Terminal capacitance | C_t | $V_R=V_{BR} \times 0.95, f=1 \text{ MHz}$ | - | 2.0 | - | pF |
| Cutoff frequency | f_c | $M=10, R_L=50 \Omega$ | - | 0.9 | - | GHz |
| Breakdown voltage | V_{BR} | $I_D=100 \mu\text{A}$ | 50 | 65 | 80 | V |
| Temperature coefficient of breakdown voltage | Γ | -40 to +85 °C | - | 0.1 | - | V/°C |
| Gain | M | $\lambda=1.55 \mu\text{m}, -30 \text{ dBm}$ | - | 30 | - | - |

Note: Attachment data: breakdown voltage ($I_D=100 \mu\text{A}$), dark current ($V_R=V_{BR} \times 0.95$), terminal capacitance ($V_R=V_{BR} \times 0.95, f=1 \text{ MHz}$), dark current vs. reverse voltage (graph), gain vs. reverse voltage (graph)

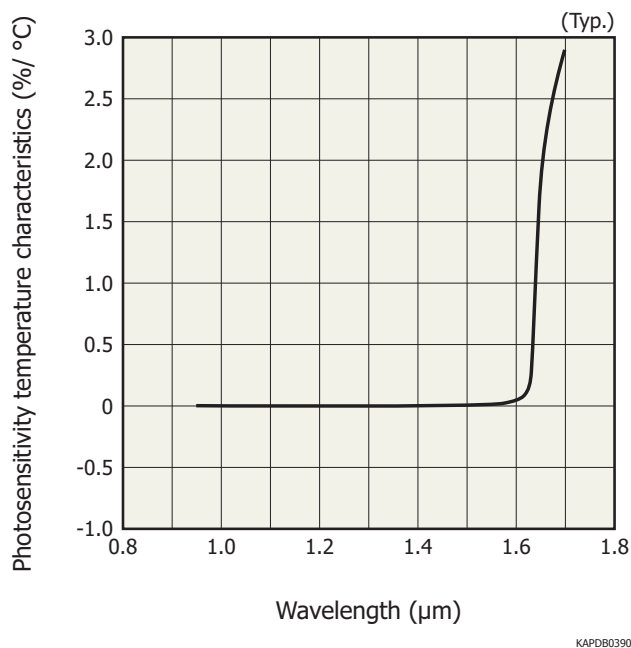
Spectral response



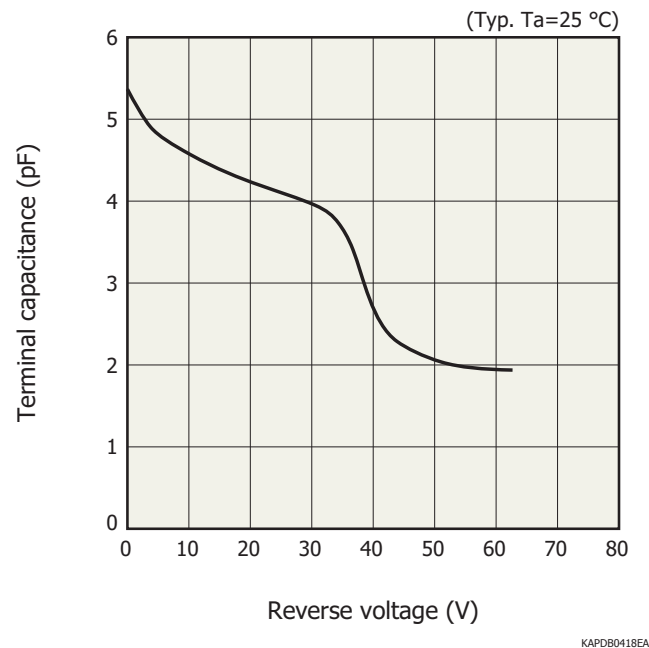
Spectral transmittance of window material



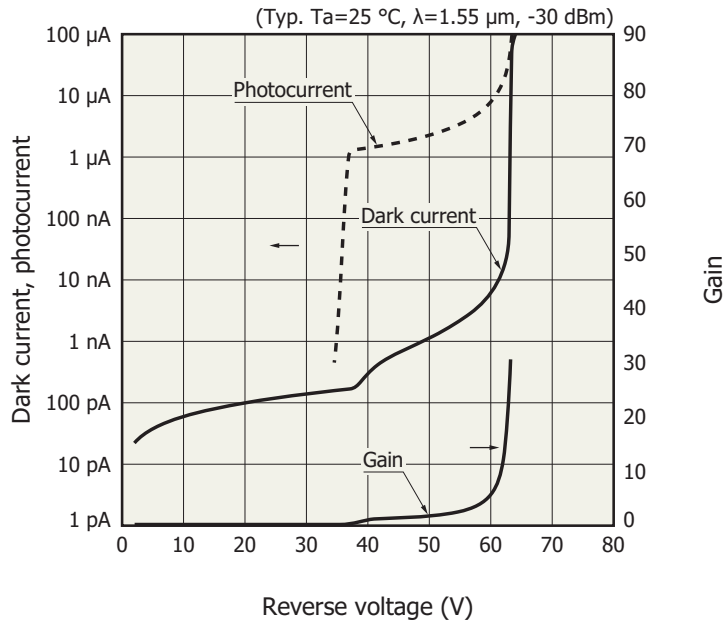
Photosensitivity temperature characteristics



Terminal capacitance vs. reverse voltage

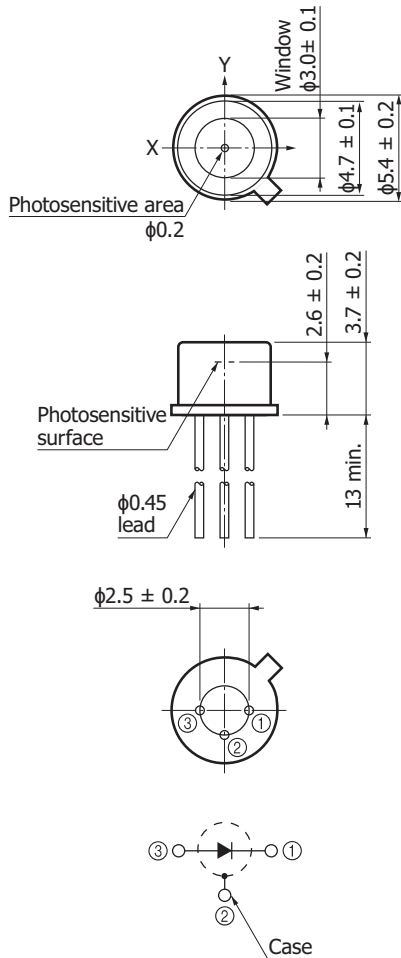


Dark current, photocurrent, gain vs. reverse voltage



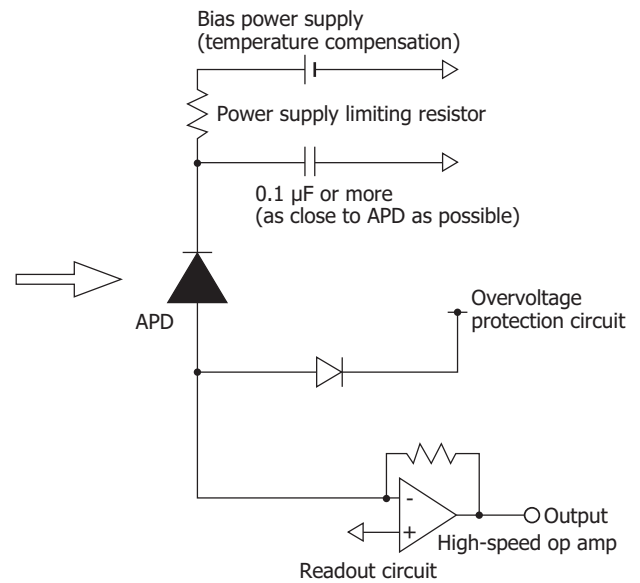
KAPD80423EA

Dimensional outline (unit: mm)



KAPDA0192EA

APD peripheral circuit example



KAPDC0005EC

Related information

www.hamamatsu.com/sp/ssd/doc_ja.html

■ Precautions

- Disclaimer
- Safety consideration
- Metal, ceramic, plastic package products

Information described in this material is current as of January 2019.

Product specifications are subject to change without prior notice due to improvements or other reasons. This document has been carefully prepared and the information contained is believed to be accurate. In rare cases, however, there may be inaccuracies such as text errors. Before using these products, always contact us for the delivery specification sheet to check the latest specifications.

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